

HETERO JUNCTION FIELD EFFECT TRANSISTOR NE350184C

K-BAND SUPER LOW NOISE AMPLIFIER N-CHANNEL HJ-FET

FEATURES

- Super low noise figure and high associated gain
 NF = 0.7 dB TYP., Ga = 13.5 dB TYP. @ f = 20 GHz
- Micro-X ceramic (84C) package

APPLICATIONS

- · 20 GHz-band DBS LNB
- · Other K-band communication systems

ORDERING INFORMATION

| Part Number | Order Number | Package | Quantity | Marking | Supplying Form |
|---------------|-----------------|---------------|-------------|---------|---|
| NE350184C-T1 | NE350184C-T1-A | 84C (Pb-Free) | 1 kpcs/reel | Α | • 12 mm wide embossed taping |
| NE350184C-T1A | NE350184C-T1A-A | | 5 kpcs/reel | | Pin 4 (Gate) faces the perforation side of the tape |

Remark To order evaluation samples, contact your nearby sales office.

Part number for sample order: NE350184C

ABSOLUTE MAXIMUM RATINGS (TA = +25°C)

| Parameter | Symbol | Ratings | Unit |
|-------------------------|-----------------------|-------------|------|
| Drain to Source Voltage | Vos | 4 | V |
| Gate to Source Voltage | Vgs | -3 | V |
| Drain Current | ΙD | Ioss | mA |
| Gate Current | lg | 80 | μА |
| Total Power Dissipation | P _{tot} Note | 165 | mW |
| Channel Temperature | Tch | +150 | °C |
| Storage Temperature | T _{stg} | -65 to +150 | °C |

Note Mounted on 1.08 cm² × 1.0 mm (t) glass epoxy PCB

Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.

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RECOMMENDED OPERATING CONDITIONS (TA = +25°C)

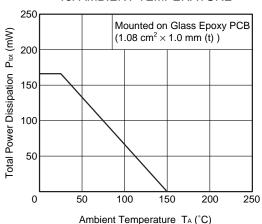
| Parameter | Symbol | MIN. | TYP. | MAX. | Unit |
|-------------------------|--------|------|------|------|------|
| Drain to Source Voltage | Vos | 1 | 2 | 3 | V |
| Drain Current | lσ | 5 | 10 | 15 | mA |
| Input Power | Pin | _ | _ | 0 | dBm |

ELECTRICAL CHARACTERISTICS (TA = +25°C)

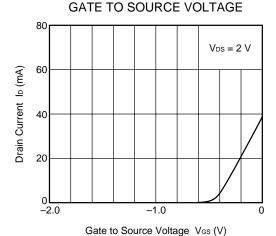
| Parameter | Symbol | Test Conditions | MIN. | TYP. | MAX. | Unit |
|-------------------------------|-----------|---|------|------|------|------|
| Gate to Source Leak Current | Igso | V _G S = −3 V | - | - | 10 | μА |
| Saturated Drain Current | IDSS | V _{DS} = 2 V, V _{GS} = 0 V | 15 | - | 70 | mA |
| Gate to Source Cutoff Voltage | VGS (off) | $V_{DS} = 2 \text{ V}, \text{ ID} = 100 \ \mu\text{A}$ | -0.2 | - | -2.0 | V |
| Transconductance | gm | V _{DS} = 2 V, I _D = 10 mA | 40 | - | - | mS |
| Noise Figure | NF | V _{DS} = 2 V, I _D = 10 mA, f = 20 GHz | - | 0.7 | 1.0 | dB |
| Associated Gain | Ga | | 11 | 13.5 | - | dB |

TYPICAL CHARACTERISTICS (TA = +25°C)

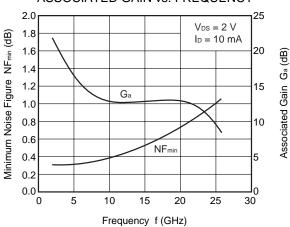
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



DRAIN CURRENT vs.

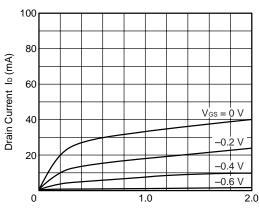


MINIMUM NOISE FIGURE, ASSOCIATED GAIN vs. FREQUENCY



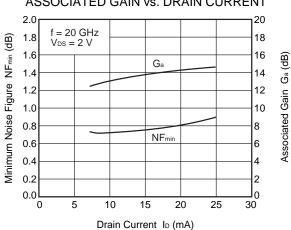
Remark The graphs indicate nominal characteristics.

DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



Drain to Source Voltage VDS (V)

MINIMUM NOISE FIGURE, ASSOCIATED GAIN vs. DRAIN CURRENT



S-PARAMETERS

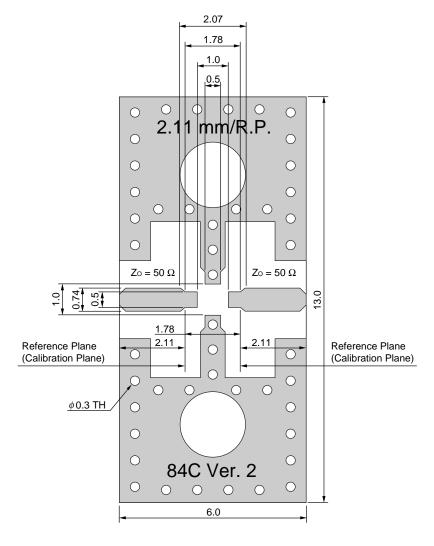
S-parameters/Noise parameters are provided on the NEC Compound Semiconductor Devices Web site in a form (S2P) that enables direct import to a microwave circuit simulator without keyboard input.

Click here to download S-parameters.

 $[\mathsf{RF} \ \mathsf{and} \ \mathsf{Microwave}] \to [\mathsf{Device} \ \mathsf{Parameters}]$

URL http://www.ncsd.necel.com/

RF MEASURING LAYOUT PATTERN (REFERENCE ONLY) (UNIT: mm)



RT/duroid 5880/ROGERS

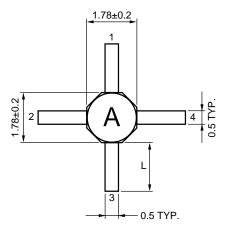
t = 0.254 mm

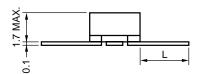
 $\varepsilon r = 2.20$

tan delta = 0.0009 @10 GHz

PACKAGE DIMENSIONS

84C (UNIT: mm)





 $L = 1.0\pm0.2$ (All leads)

PIN CONNECTIONS

- 1. Source
- 2. Drain
- 3. Source
- 4. Gate

RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

| Soldering Method | Soldering Conditions | | Condition Symbol |
|------------------|---|---|------------------|
| Infrared Reflow | Peak temperature (package surface temperature) Time at peak temperature Time at temperature of 220°C or higher Preheating time at 120 to 180°C Maximum number of reflow processes Maximum chlorine content of rosin flux (% mass) | : 260°C or below : 10 seconds or less : 60 seconds or less : 120±30 seconds : 3 times : 0.2%(Wt.) or below | IR260 |
| Partial Heating | Peak temperature (terminal temperature) Soldering time (per side of device) Maximum chlorine content of rosin flux (% mass) | : 350°C or below : 3 seconds or less : 0.2%(Wt.) or below | HS350 |

Caution Do not use different soldering methods together (except for partial heating).



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Subject: Compliance with EU Directives

CEL certifies, to its knowledge, that semiconductor and laser products detailed below are compliant with the requirements of European Union (EU) Directive 2002/95/EC Restriction on Use of Hazardous Substances in electrical and electronic equipment (RoHS) and the requirements of EU Directive 2003/11/EC Restriction on Penta and Octa BDE.

CEL Pb-free products have the same base part number with a suffix added. The suffix –A indicates that the device is Pb-free. The –AZ suffix is used to designate devices containing Pb which are exempted from the requirement of RoHS directive (*). In all cases the devices have Pb-free terminals. All devices with these suffixes meet the requirements of the RoHS directive.

This status is based on CEL's understanding of the EU Directives and knowledge of the materials that go into its products as of the date of disclosure of this information.

| Restricted Substance per RoHS | Concentration Limit per RoHS (values are not yet fixed) | | on contained devices |
|-------------------------------|---|--------------------|-------------------------|
| Lead (Pb) | < 1000 PPM | -A Not Detected | -AZ (*) |
| Mercury | < 1000 PPM | Not Detected | |
| Cadmium | < 100 PPM | Not Detected | |
| Hexavalent Chromium | < 1000 PPM | Not Detected | |
| PBB | < 1000 PPM | Not Detected | |
| PBDE | < 1000 PPM | Not Detected | |

If you should have any additional questions regarding our devices and compliance to environmental standards, please do not hesitate to contact your local representative.

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